

109 學年度四技二專第三次聯合模擬考試

電機與電子群 專業科目(一) 詳解

109-3-03-4、109-3-04-4

1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25
A	D	B	D	B	A	C	C	B	C	A	A	B	C	B	C	C	B	D	B	D	D	B	C	B
26	27	28	29	30	31	32	33	34	35	36	37	38	39	40	41	42	43	44	45	46	47	48	49	50
B	D	C	B	D	C	A	A	B	C	D	C	D	A	B	C	A	A	C	D	D	A	D	A	B

第一部分：電子學

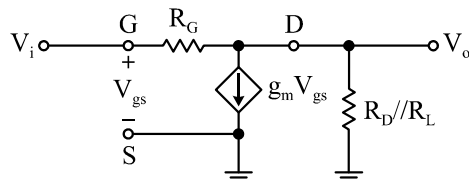
- (A) 週期 $T = \frac{4 \times 10^{-3}}{8} = 0.5 \times 10^{-3} = 0.5 \text{ ms}$
 頻率 $f = \frac{1}{0.5 \times 10^{-3}} = 2 \times 10^3 = 2 \text{ kHz}$
- (D) P 型及 N 型半導體均為電中性
- $I_Z = I_S - I_L \Rightarrow I_Z = \frac{V_i - V_Z}{R_S} - \frac{V_Z}{R_L} = \frac{V_i - 8}{0.5} - \frac{8}{R_L}$
 $\Rightarrow I_{Z(\max)} = \frac{V_{i(\max)} - 8}{0.5} - \frac{8}{R_{L(\max)}} = \frac{30 - 8}{0.5} - \frac{8}{0.8}$
 $= 34 \text{ mA}$
 $\therefore P_{Z(\max)} = V_Z \times I_{Z(\max)} = 8 \times 34 = 272 \text{ mW}$
- 負半週無法使 V_{Z1} 產生崩潰，但正半週可使 V_{Z2} 產生崩潰，因此繪出曲線圖可得知 v_o 範圍為 $0 \text{ V} \leq v_o \leq 2.4 \text{ V}$
- (B) 橋式全波整流之二極體 PIV 額定值為 $V_m = 31.8 \div 0.636 = 50 \text{ 伏特}$
- 因稽納二極體持續順向導通，因此視為短路，故輸出電壓為 0 V
- (C) NPN 電晶體的頻率特性優於 PNP 電晶體
- $\beta = \frac{\alpha}{1 - \alpha} = \frac{0.975}{1 - 0.975} = 39$
- $V_{CC} = I_{C(\min)} R_{C(\max)} + V_{LED(\min)} + V_{CE}$
 $6.6 = 12 \text{ m} \times R_{C(\max)} + 3 \quad \therefore R_{C(\max)} = 300 \Omega$
 $I_{B(\min)} = \frac{I_{C(\min)}}{\beta} = \frac{12 \text{ mA}}{200} = 60 \mu\text{A}$
 $V_{BB} = I_{B(\min)} R_{B(\max)} + V_{BE}$
 $4.8 = 60 \mu \times R_{B(\max)} + 0.6 \quad \therefore R_{B(\max)} = 70 \text{ k}\Omega$
 $V_{CC} = I_{C(\max)} R_{C(\min)} + V_{LED(\max)} + V_{CE}$
 $6.6 = 20 \text{ m} \times R_{C(\min)} + 5 \quad \therefore R_{C(\min)} = 80 \Omega$
 $I_{B(\max)} = \frac{I_{C(\max)}}{\beta} = \frac{20 \text{ mA}}{200} = 100 \mu\text{A}$
 $V_{BB} = I_{B(\max)} R_{B(\min)} + V_{BE}$
 $4.8 = 100 \mu \times R_{B(\min)} + 0.6 \quad \therefore R_{B(\min)} = 42 \text{ k}\Omega$
 只有(B)選項的電阻不合範圍
- $V_{BB} = 9.9 \times \frac{588 \text{ k}}{294 \text{ k} + 588 \text{ k}} = 6.6 \text{ V}$
 $R_{BB} = R_{B1} // R_{B2} = 196 \text{ k}\Omega$

$$I_B = \frac{V_{BB} - V_{BE}}{R_{BB} + (1 + \beta)R_E} = \frac{6.6 - 0.6}{196 \text{ k} + 404 \text{ k}} = \frac{6}{600 \text{ k}} = 10 \mu\text{A}$$

$$I_C = \beta I_B = 100 \times 10 \mu = 1 \text{ mA}$$

$$I_{C(\text{sat})} = \frac{9.9 - 0.2}{6 \text{ k} + 4 \text{ k}} = 0.97 \text{ mA}$$

$\therefore$ 此電路已進入飽和區， $V_{CE} \doteq 0.2 \text{ V}$

- (A) 此為 CE 電路輸出特性曲線
- (A) A 接 V_o 、B 接 V_i 、C 接直流電源，可完成共基極 (CB) 組態
- $I_E = (1 + \beta) \times I_B = (1 + 199) \times 12.5 \mu = 2.5 \text{ mA}$
 $r_e = \frac{V_T}{I_E} = \frac{25 \text{ m}}{2.5 \text{ m}} = 10 \Omega$
- 最大電壓增益為 $\sqrt{2}$ 倍截止頻率增益
 $\therefore \sqrt{2} \times 100 \sqrt{2} = 200$
- $-20 \text{ dBm} = 20 \log \frac{V_o}{0.775} \Rightarrow \log \frac{V_o}{0.775} = -1$
 $\Rightarrow V_o = 0.0775 \text{ V}$
- (C) 電流增益極大，電壓增益極小
- (A) 利用外加電壓大小控制空乏區厚度
 (B) 增強型 MOSFET 須外加電壓產生通道
 (D) CMOS 邏輯電路消耗功率極小
- $I_D = K \times (V_{GS} - V_T)^2 = 0.5 \times (6 - 4)^2 = 2 \text{ mA}$
- 空乏型 NMOS 在飽和區工作
 須滿足 $V_{GS} > V_P$ 及 $V_{GD} \leq V_P$
 $V_{GS} > V_P \Rightarrow V_G - V_S > V_P \Rightarrow V_G - (-3) > -5$
 $\therefore V_G > -8$
 $V_{GD} \leq V_P \Rightarrow V_G - V_D \leq V_P \Rightarrow V_G - 2 \leq -5$
 $\therefore V_G \leq -3$
 故 $-8 < V_G \leq -3$ ，故選(D)
- $A_v = \frac{-g_m V_{gs} \times R_D}{V_{gs} + g_m V_{gs} \times R_S} \Rightarrow -4.75 = \frac{-g_m \times 25 \text{ k}}{1 + g_m \times 5 \text{ k}}$
 $\Rightarrow g_m = 3.8 \text{ mA/V}$
- 

R_G 電阻極大，可不考慮

- $V_{GS} = V_{DS} = V_{DD} - I_D R_D = 5 - 0.2 \times 5 = 4 \text{ V}$
 $I_D = K(V_{GS} - V_T)^2 \Rightarrow 0.2 = K(4 - 2)^2$
 $\Rightarrow K = 0.05 \text{ mA/V}^2$
 $g_m = 2K(V_{GS} - V_T) = 2 \times 0.05 \times (4 - 2) = 0.2 \text{ mA/V}$
 $A_v = \frac{V_o}{V_i} = \frac{-g_m V_{gs}(R_D // R_L)}{V_{gs}} = -g_m(R_D // R_L)$
 $= -0.2 \text{ mA/V} \times (5 \text{ k}\Omega // 20 \text{ k}\Omega) = -0.8$
22. $I_{D1} = I_{D2} \Rightarrow K_1(V_{GS1} - V_{T1})^2 = K_2(V_{GS2} - V_{T2})^2$
 $\Rightarrow \frac{V_{GS1} - V_{T1}}{V_{GS2} - V_{T2}} = \sqrt{\frac{K_2}{K_1}} \Rightarrow \frac{2K_1(V_{GS1} - V_{T1})}{2K_2(V_{GS2} - V_{T2})} = \frac{K_1}{K_2} \times \sqrt{\frac{K_2}{K_1}}$
 $\Rightarrow \frac{g_{m1}}{g_{m2}} = \sqrt{\frac{K_1}{K_2}}$
 且 $g_{m1} V_{gs1} = g_{m2} V_{gs2} \Rightarrow \frac{V_{gs2}}{V_{gs1}} = \frac{g_{m1}}{g_{m2}}$
 $\therefore \frac{V_o}{V_s} = -\frac{V_{gs2}}{V_{gs1}} = -\frac{g_{m1}}{g_{m2}} = -\sqrt{\frac{K_1}{K_2}}$
 $\therefore -8 = -\sqrt{\frac{16}{K_2}} \Rightarrow 64 = \frac{16}{K_2} \Rightarrow K_2 = 0.25$
23. $f_{\max} = \frac{SR}{2\pi V_m} \Rightarrow 50 \text{ kHz} = \frac{1.884 \text{ V}/\mu\text{S}}{2 \times 3.14 \times V_m} \therefore V_m = 6 \text{ V}$
24. (C) 理想運算放大器之輸入阻抗無限大
25. 甲：不可用短路線接一起
 乙： $A_{V(\max)} = 1 + \frac{16}{2} = 9$
 丙： $f_H = \frac{1}{2\pi R_i C} = \frac{1}{2 \times 3.14 \times 10 \times 10^3 \times 0.01 \times 10^{-6}}$
 $\approx 1592 \text{ Hz} \approx 1.6 \text{ kHz}$
 丁： -3 dB 截止頻率為半功率點
 戊：當高頻高於 f_{OH} 時，衰減斜率為每 10 倍頻率為 $20 \text{ dB} (-20 \text{ dB/dec})$

第二部分：基本電學

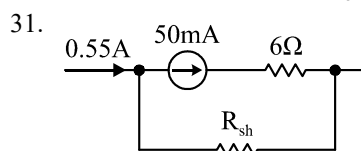
26. $P_o = 1000 - 370 = 630 \text{ W}$
 $\eta = \frac{P_o}{P_i} = \frac{630}{1000} = 0.63$
 $\eta = \eta_1 \times \eta_2 \Rightarrow 0.63 = 0.7 \times \eta_2 \Rightarrow \eta_2 = 0.9 = 90\%$
27. $W = QV = ItV = Pt$
 $\Rightarrow 1200 \times 10^{-3} \times 60 \times 60 \times 3.6 = 0.018 \times t$
 $\Rightarrow t = 864000 \text{ 秒} = 240 \text{ 小時}$
28. 該電流變動範圍為 $800 \pm 4 \text{ mA}$ ，電流誤差 0.5%
 (A)(B) 電阻均誤差 5%
 (C) 電阻誤差 0.5%
 (D) 電阻誤差 10%
 $\therefore I = \frac{V}{R}$ ，所以電阻誤差變動即為電流誤差變動
29. $H = 0.24Pt = ms\Delta T$

$$(0.24 \times \frac{110^2}{11} - 4) \times t = 2600 \times 1 \times (100 - 25)$$

$$\therefore t = 750 \text{ 秒}$$

30. $\therefore P = \frac{V^2}{R} \rightarrow R = \frac{V^2}{P}$ ，且並聯端電壓相等

$$R_1 : R_2 : R_3 = \frac{1}{P_1} : \frac{1}{P_2} : \frac{1}{P_3} = \frac{1}{9} : \frac{1}{3} : \frac{1}{2} = 2 : 6 : 9$$



$$50 \text{ mA} \times 6 \Omega = 0.5 \text{ A} \times R_{sh} \therefore R_{sh} = 0.6 \Omega$$

32. 開關閉合前， $I = 0 \text{ A}$

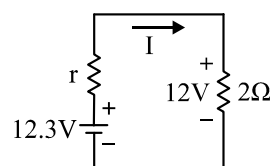
電源電壓 $E = 12.3 \text{ V}$

開關閉合後， $V_{2\Omega} = 12 \text{ V}$

$$I = \frac{12}{2} = 6 \text{ A}$$

$$\therefore 12.3 = 6r + 12 \Rightarrow r = 0.05 \Omega$$

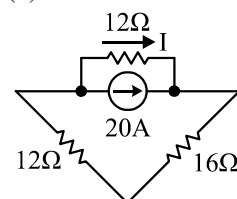
$$V.R.\% = \frac{12.3 - 12}{12} \times 100\% = 2.5\%$$



33. 運用重疊定理：

(1) 電流源開路考慮 12 V 電壓源時，該電路為惠斯登電橋，因此 $I = 0 \text{ A}$

(2) 電壓源短路考慮 5 A 的電流源時，電路如下：

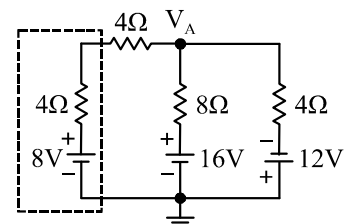


$$I = -20 \times \frac{(12+16)}{(12+16)+12} = -14 \text{ A}$$

34. 2Ω 電阻兩端電壓為 6 V ， 12 A 電流未流過 2Ω 電阻

$$\therefore I = \frac{-6}{2} = -3 \text{ A}$$

35.



將左側電路等效後，利用節點電壓法求解

$$\frac{V_A - 8}{4+4} + \frac{V_A - 16}{8} + \frac{V_A + 12}{4} = 0 \therefore V_A = 0 \text{ V}$$

$$I = \frac{0 - 8}{4+4} = -1 \text{ A}$$

36. R 短路時， 24Ω 可得最大電壓及功率

37. $C = \epsilon \frac{A}{d}$ ，極板間距減半電容量變為原來的 2 倍，且將電源移除後電荷守恒

$$W = \frac{1}{2} \frac{Q^2}{C} \Rightarrow 64 : W = \frac{1}{2} \frac{Q^2}{C} : \frac{1}{2} \frac{Q^2}{2C}$$

$$\Rightarrow 64 : W = \frac{1}{2} : \frac{1}{4} \Rightarrow W = 32 \text{ J (焦耳)}$$

$$38. E = \frac{F}{Q} = \frac{0.03}{150 \times 10^{-6}} = 200 \text{ Nt/C}$$

39. (A) 儲存能量且電位減小

40. (1) 根據佛萊銘左手定則，導體運動向上

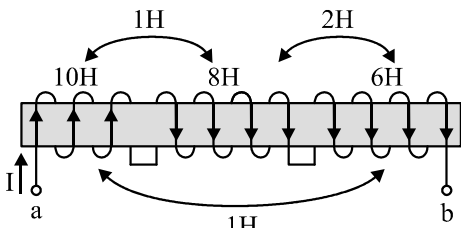
(2) 受力大小 $F = B \times \ell \times I \times \sin \theta$

$$\Rightarrow F = \frac{4000}{10^4} \times \frac{20}{100} \times 4 \times \sin 90^\circ = 0.32 \text{ 牛頓}$$

41. (1) 依據電流方向判斷互助或互消

$$(2) L_{ab} = (10 - 1 - 1) + (8 - 1 + 2) + (6 + 2 - 1) = 24 \text{ H}$$

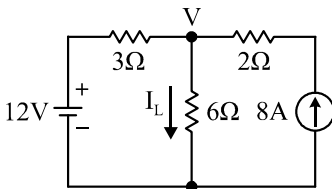
$$(3) W = \frac{1}{2} \times L_{ab} \times I^2 = \frac{1}{2} \times 24 \times \sqrt{5}^2 = 60 \text{ J (焦耳)}$$



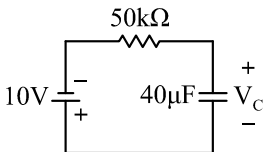
42. (1) 穩態時電感器短路，電容器開路

$$(2) \text{運用密爾門定理：} V = \frac{\frac{12}{\frac{3}{1} + \frac{8}{6}}}{\frac{1}{3} + \frac{1}{6}} = 24 \text{ V}$$

$$(3) I_L = \frac{24}{6} = 4 \text{ A}$$



43. 將電路化為戴維寧等效電路如下圖



$$\tau = RC = 50 \text{ k} \times 40 \mu = 2 \text{ 秒}$$

$$V_{C(t=6)} = -10 \times (1 - e^{-\frac{t}{\tau}}) = -10 \times (1 - e^{-\frac{6}{2}})$$

$$= -10 \times (1 - e^{-3}) = -10 \times (1 - 0.05) = -9.5 \text{ V}$$

$$44. i_2(t) = -\sin(\omega t + 60^\circ) = \sin(\omega t + 240^\circ) = \cos(\omega t + 150^\circ)$$

$\therefore i_1$ 與 i_2 相位相差 180°

$$45. V = 200 \sin(377t - 30^\circ) + 200 \cos(377t - 30^\circ)$$

$$= 200\sqrt{2} \sin(377t + 15^\circ)$$

$$V_{\text{rms}} = \frac{200\sqrt{2}}{\sqrt{2}} = 200 \text{ V}$$

46. (1) 串聯互消

$$L_T = L_1 + L_2 - 2M = 12 \text{ mH} + 16 \text{ mH} - 2 \times 4 \text{ mH}$$

$$= 20 \text{ mH}$$

$$(2) X_L = j\omega L = 1 \angle 90^\circ \Omega$$

$$(3) i(t) = 100\sqrt{2} \sin(50t - 135^\circ)$$

$$= -100\sqrt{2} \sin(50t + 45^\circ)$$

$$47. (1) V_1 = \sqrt{(4 \times 15)^2 + (4 \times 20)^2} = 100 \text{ V}$$

$$(2) V_2 = 4 \times 20 - 4 \times 20 = 0 \text{ V}$$

$$48. (A) v_i(t) = 200\sqrt{2} \sin 1000t$$

$$(B)(C) X_C = \frac{1}{2 \times 3.14 \times 159 \times 0.1 \mu} \cong 10 \text{ k}\Omega$$

$$V_A = 200 \times \frac{20 \text{ k}}{20 \text{ k} + 20 \text{ k}} = 100 \angle 0^\circ \text{ V}$$

$$V_B = 200 \times \frac{-j10 \text{ k}}{10 \text{ k} - j10 \text{ k}} = 100\sqrt{2} \angle -45^\circ \text{ V}$$

$\therefore A$ 點電壓超前 B 點電壓 45°

$$(D) V_A = 200 \times \frac{20 \text{ k}}{20 \text{ k} + 20 \text{ k}} = 100 \text{ V}$$

穩態時 $V_B = 200 \text{ V}$

$$\therefore V_{AB} = 100 - 200 = -100 \text{ V}$$

$$49. P_s = P_p \times \cos^2 \theta_s \Rightarrow 540 = P_p \times 0.6^2$$

$$\therefore P_p = 1500 \text{ W}$$

$$50. I_1 = 0 \text{ (因 } I_3 \text{ 迴路諧振造成短路)}$$

$$I_2 = 0 \text{ (因 } I_3 \text{ 迴路諧振造成短路)}$$

I_3 迴路因感抗與容抗大小相等，因此該迴路電流為無限大，線路總電流 I 亦為無限大